CHENMKO ENTERPRISE CO.,LTD

CH425DGP

Halogens free devices

SURFACE MOUNT

SCHOTTKY BARRIER DIODE

VOLTAGE 40 Volts CURRENT 0.1 Ampere

APPLICATION

* Low power rectification

FEATURE

* Small surface mounting type. (SOT-23)
* Low VF. (VF=0.45V Typ. at 100mA)
* High reliability

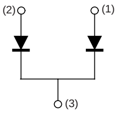
CONSTRUCTION

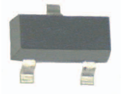
* Silicon epitaxial planar

MARKING

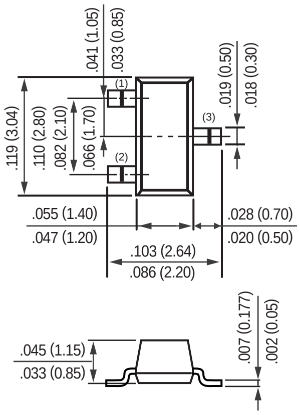
* KL4

CIRCUIT





SOT-23



Dimensions in millimeters

SOT-23

MAXIMUM RATINGES (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH425DGP	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	Volts
Maximum RMS Voltage	V_{RMS}	28	Volts
Maximum DC Blocking Voltage	V_{DC}	40	Volts
Maximum Average Forward Rectified Current	I_O	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	I_{FSM}	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	C_J	6.0	pF
Maximum Operating Temperature Range	T_J	+125	°C
Storage Temperature Range	T_{STG}	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH425DGP	UNITS
Maximum Instantaneous Forward Voltage at $I_F(1)$= 10mA	$V_F(1)$	0.34	Volts
Maximum Instantaneous Forward Voltage at $I_F(2)$= 100mA	$V_F(2)$	0.55	Volts
Maximum Average Reverse Current at V_R= 10V	I_R	30	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.
2. ESD sensitive product handling required.

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RATING CHARACTERISTIC CURVES (CH425DGP)

FIG. 1 - FORWARD CHARACTERISiTICS

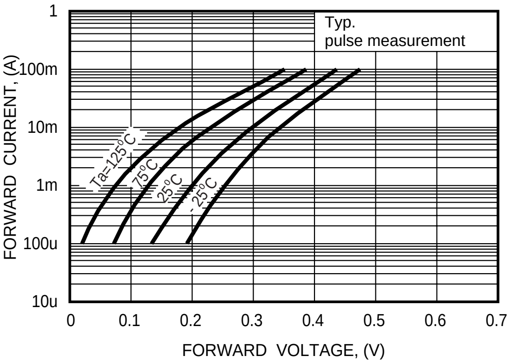

FIG. 2 - REVERSE CHARACTERISTICS

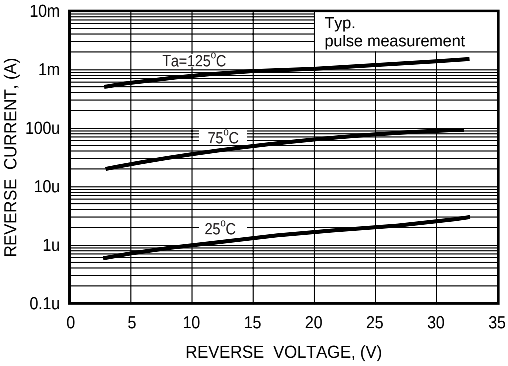

FIG. 3 - TYPICAL JUNCTION CAPACITANCE

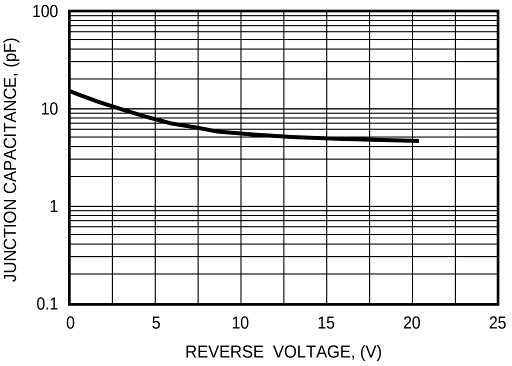

FIG. 4 - TYPICAL FORWARD CURRENT DERAING CURVE